

INFORMATION DISCLOSURE  
CITATION

ATTY. DOCKET NO.

340-81

SERIAL NO.

10/686,519

APPLICANT

KOCHERGIN ET AL.

FILING DATE

16 October 2003

TC/A.U.

2872

(Use several sheets if necessary)



## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AN	4,874,484	10/1989	Foell et al.			
	5,262,021	11/1993	V. Lehmann et al.			
	5,348,627	09/1994	Propst et al.			
	5,431,766	07/1995	Propst et al.			
AN	5,544,772	08/1996	Soave et al.			
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	5,987,208	11/1999	Grunig			
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AN	6,521,149	02/2003	Mearini et al.			
AN	6,526,191	02/2003	Geusic et al.			

## FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
AN	3717851	Germany			
AN	4202454	Germany			

## OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

AN	Lehmann et al., Optical shortpass filters based on macroporous silicon <i>Appl. Phys. Lett.</i> V 78, N.5, Jan. 2001.
AN	J. Schilling et al., "Three-dimensional photonic crystals based on Macroporous silicon with modulated pore diameter", <i>Appl. Phys. Lett.</i> V 78, N.9, Feb. 2001
AN	S. Izuo et al., "A novel electrochemical etching technique for n-type silicon," <i>Sensors and Actuators A</i> 97-98 (2002), pp. 720-724 (no month)
AN	A. Vyatkin et al., "Random and Ordered Macropore Formation in p-Type Silicon," <i>J. of the Electrochem. Soc.</i> , 149 (1), pp. G70-G76 (2002) (no month)
AN	H. Föll et al., "Formation and application of porous silicon", <i>Mat. Sci. Eng. R</i> 39.(2002), pp.93-141 (no month)
AN	S. Langa et al., "Observation of crossing pores in anodically etched n-GaAs," <i>Appl. Phys. Lett.</i> 78(8), pp.1074-1076, (2001) (no month)
AN	H. H. Föll et al., "Porous III-V compound semiconductors: formation, properties, and comparison to silicon", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 61-70 (2003) (no month)
AN	M. Christophersen et al., "A comparison of pores in silicon and pores in III-V compound materials", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 197-203, (2003) (no month)
AN	H. Föll et al., "Pores in III-V Semiconductors", <i>Adv. Materials, Review</i> , 2003, 15, pp.183 - 198, (2003) (no month)
AN	S. Langa et al., <i>Phys. Stat. Sol. A</i> , 197 (1), p. 77, (2003) "Single crystalline 2D porous arrays obtained by self organization in n-InP" (pp. 77-82) (no month)

\*Examiner

Donald R. Valentini

Date Considered

8-6-04

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

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OK	K. Barla et al., "X-Ray Topographic Characterization of Porous Silicon Layers," <i>J. Cryst. Growth</i> , <b>68</b> , North-Holland, Amsterdam, p. 721-726 (1984) (no month)
OK	B.H. Erne et al., "Porous Etching: A Means to Enhance the Photo response of Indirect Semiconductors," <i>Adv. Mater.</i> , <b>7</b> , p. 739-742 (1995) (no month)
OK	P.A. Kohl et al., <i>J. Electrochem. Soc.</i> , <b>130</b> (11), "The Photoelectrochemical Oxidation of (100), (111), and (111) n-InP and n-GaAs," p. 2288-2293 (11/1983)
OK	Schmuki P. et al., <i>Physica Status Solidi A</i> , "Pore Formation on n-InP," <b>182</b> (1), pp. 51-61, (2000) (no month)
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OK	S. Langa et al., <i>Phys. Stat. Sol. (A)</i> , <b>195</b> (3), "Electrochemical pore etching in Ge," R4-R6 (2003) (no month)
OK	Macleod H.A., <i>Thin-Film Optical Filters</i> , 3rd ed., Institute of Physics Publishing, 2001 (no month)
OK	D.J. Lockwood et al., "Optical properties of porous GaAs," <i>Physica E</i> , <b>4</b> , pp. 102-110 (1999) (no month)
OK	Schmuki, P. et al., "Formation of porous layers on InSb(100) by anodization," <i>Phys. Stat. Sol. (a)</i> <b>197</b> , No. 1, pp. 71-76 (2003) (no month)
OK	Langa, S. et al., "Voltage oscillations - an emergent property at high density pore growth," <i>Phys. Stat. Sol. (a)</i> <b>197</b> , No. 1, pp. 186-191 (2003) (no month)

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